

Complementary power transistors

Features

- Low collector-emitter saturation voltage
- Complementary NPN PNP transistors

Applications

■ General purpose

Description

The devices are manufactured in epitaxial-base planar technology and are suitable for power linear and switching applications.

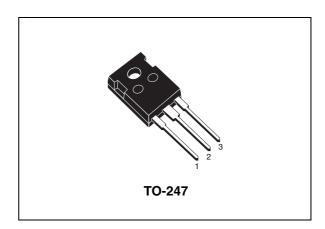


Figure 1. Internal schematic diagrams

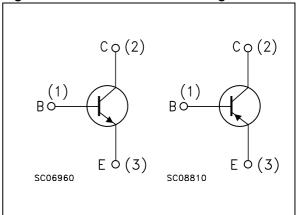


Table 1. Device summary

Order code	Marking	Package	Packaging
TIP33C	TIP33C	TO-247	Tube
TIP34C	TIP34C	10-247	lube

Electrical ratings TIP34C

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter		Value	Unit
		NPN	TIP33C	
		PNP	TIP34C	
V _{CBO}	Collector-base voltage (I _E = 0)	•	140	V
V _{CES}	Collector-emitter voltage (V _{BE} = 0)		140	V
V _{CEO}	Collector-emitter voltage (I _B = 0)		100	V
V _{EBO}	Emitter-base voltage (I _C = 0)		5	V
I _C	Collector current		10	Α
I _{CM}	Collector peak current (t _P < 5 ms)		15	Α
I _B	Base current		3	Α
P _{TOT}	Total dissipation at T _{case} = 25 °C		80	W
T _{stg}	Storage temperature		-65 to 150	°C
TJ	Max. operating junction temperature		150	°C

For PNP type voltage and current values are negative.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	1.56	°C/W

2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C; \, unless \, otherwise \, specified)$

Table 4. Electrical characteristics

Symbol	Parameter	Test condi	tions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	V _{CE} = 140 V				0.4	mA
I _{CEO}	Collector cut-off current (I _B = 0)	V _{CE} = 60 V				0.7	mA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 5 V				1	mA
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	I _C = 30 mA		100			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = 3 A I _C = 10 A	$I_B = 0.3 A$ $I_B = 2.5 A$			1 4	V V
V _{BE(on)} ⁽¹⁾	Base-emitter voltage	I _C = 3 A I _C = 10 A	V _{CE} = 4 V V _{CE} = 4 V			1.6 3	V V
h _{FE} ⁽¹⁾	DC current gain	•	V _{CE} = 4 V V _{CE} = 4 V	40 20		100	
h _{fe}	Small signal current gain	I _C = 0.5 A f = 1 kHz	V _{CE} = 10 V	3			
f _T	Transition frequency	I _C = 0.5 A f = 1 MHz	V _{CE} = 10 V	3			MHz
t _{on} t _s	Resistive load Turn-on time Storage time Fall time	$V_{CC} = 30 \text{ V}$ $I_{B1} = -I_{B2} = 0.6 \text{ A}$ $tp = 20 \mu\text{s}$	-		0.6 0.4 1		μs μs μs

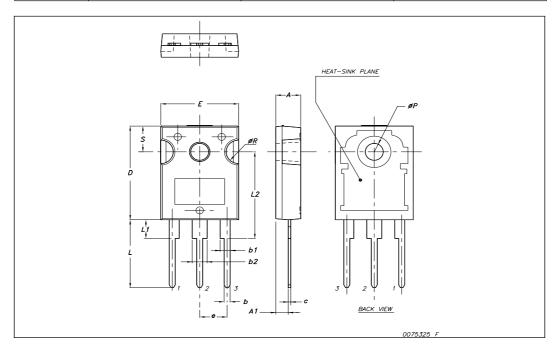
^{1.} Pulsed duration = 300 ms, duty cycle \geq 1.5%.

3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-247 Mechanical data

Dim.	mm.				
	Min.	Тур	Max.		
Α	4.85		5.15		
A1	2.20		2.60		
b	1.0		1.40		
b1	2.0		2.40		
b2	3.0		3.40		
С	0.40		0.80		
D	19.85		20.15		
E	15.45		15.75		
е		5.45			
L	14.20		14.80		
L1	3.70		4.30		
L2		18.50			
øΡ	3.55		3.65		
øR	4.50		5.50		
S		5.50			



577

Revision history TIP34C

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
01-Oct-1999	2	
20-Feb-2008	3	Package change from TO-218 to TO-247.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2008 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

